10-728,909

SHEET 1 OF 1

| INFORMATION DISCLOSURE CITATION PTO-1449 | Customer Number 26615 | ATTORNEY'S DKT NO. H1124 | APPLICATION NO. Unassigned |
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| | | APPLICANT(S) Cyrus E. Tabery et al. | |
| | | FILING DATE December 8, 2003 | GROUP Unassigned 1763 |

**U.S. PATENT DOCUMENTS**

| EXAMINER'S INITIALS | PATENT NO. | DATE | NAME | CLASS | SUBCLASS | FILING DATE |
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**FOREIGN PATENT DOCUMENTS**

| EXAMINER'S INITIALS | PATENT NO. | DATE | COUNTRY | CLASS | SUBCLASS | Translation Yes | Translation No |
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| EXAMINER George Gaudreau | DATE CONSIDERED 7-05 |
|---|---|

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).